

# **isc Silicon PNP Power Transistor**

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -60V(Min)
- · Low Collector Saturation Voltage-
- :  $V_{CE(sat)} = -1.0V(Max)@ (I_C = -2A, I_B = -0.2A)$
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

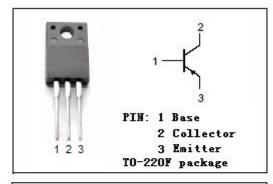
### **APPLICATIONS**

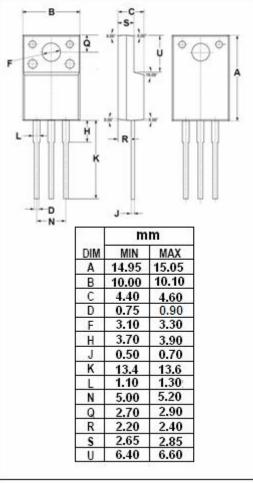
· Designed for power amplifications.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-80	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V	
Ic	Collector Current-Continuous	-3	Α	
Ісм	Collector Current-Peak	-6	Α	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	25		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$	







## isc Silicon PNP Power Transistor

2SB1655

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I <sub>C</sub> = -50 μ A; I <sub>E</sub> = 0	-80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -50 μ A; I <sub>C</sub> = 0	-7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -60V; I <sub>E</sub> = 0			-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> = 0			-10	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -5V	100		200	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A;V <sub>CE</sub> = -5V; f <sub>test</sub> = 5MHz		15		MHz
Сов	Collector Output Capacitance	I <sub>E</sub> = 0;V <sub>CE</sub> = -10V; f <sub>test</sub> = 1MHz		50		pF

### **NOTICE:**

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